

Description

The AP9926GM uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

D1_{D1}_{D2}_{D2} S1_{G1}_{S2}_{G2} SOP-8

General Features

V_{DS} = 20V I_D = 6A

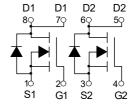
 $R_{DS(ON)} < 25m\Omega$ @ $V_{GS}=4.5V$

Application

Battery protection

Load switch

Uninterruptible power supply



Dual N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
AP9926GM	SOP-8	HXY MOSFET	3000

Absolute Maximum Ratings@Tj=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	20	V
V _G S	Gate-Source Voltage	<u>+</u> 12	V
I _D @T _A =25°C	Drain Current, V _{GS} @ 4.5V ³	6	А
ID@TA=70°C	Drain Current, V _{GS} @ 4.5V ³	4.8	А
Ірм	Pulsed Drain Current ¹	26	А
P _D @T _A =25°C	Total Power Dissipation	2	W
	Linear Derating Factor	0.016	W/°C
Тѕтс	Storage Temperature Range	-55 to 150	℃
TJ	Operating Junction Temperature Range	-55 to 150	°C
Rthj-a	Maximum Thermal Resistance, Junction- ambient ³	62.5	°C/W



Electrical Characteristics@T_j=25 °C(unless otherwise specified)

		sas otherwise specified)				
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	20	-	-	V
` '	Static Drain-Source On- Resistance ²	V _{GS} =4.5V, I _D =6A	-	21	25	mΩ
		V _{GS} =2.5V, I _D =4A	-	32	45	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	-	1.2	3	V
g fs	Forward Transconductance	V _{DS} =10V, I _D =6A	ı	6	-	S
IDSS	Drain-Source Leakage Current	V _{DS} =20V, V _{GS} =0V	-	-	25	uA
	Drain-Source Leakage Current (Tj=70°C)	V _{DS} =20V ,V _{GS} =0V	ı	-	250	uA
Igss	Gate-Source Leakage	V _{GS} = <u>+</u> 12V, V _{DS} =0V	-	-	<u>+</u> 100	nA
Qg	Total Gate Charge ²	I _D =6A	-	11	17.6	nC
Q _{gs}	Gate-Source Charge	V _{DS} =16V V _{GS} =4.5V	-	1.1	-	nC
Qgd	Gate-Drain ("Miller") Charge		ı	4.1	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =10V	ı	4.2	-	ns
t _r	Rise Time	I _D =1A	-	9	-	ns
t _{d(off)}	Turn-off Delay Time	R _D =3.3Ω,V _{GS} =10V	-	23	-	ns
t _f	Fall Time	1075	-	3.5	-	ns
Ciss	Input Capacitance		-	570	910	pF
Coss	Output Capacitance	V _{GS} =0V	-	90	-	pF
Crss	Reverse Transfer Capacitance	V _{DS} =20V f=1.0MHz	-	85	-	pF
Rg	Gate Resistance	f=1.0MHz	-	1.6	2.4	Ω
V _{SD}	Forward On Voltage ²	I _S =1.7A, V _{GS} =0V	ı	-	1.2	V
t _{rr}	Reverse Recovery Time ²	Is=6A, V _{GS} =0V,	-	21	-	ns
Qrr	Reverse Recovery Charge	dI/dt=100A/μs	-	14	-	nC

Notes:

- 1. Pulse width limited by Max. junction temperature.
- 2 Pulse test
- 3.Surface mounted on 1 in 2 copper pad of FR4 board, t \leq 10sec ; 135 °C/W when mounted on Min. copper pad.



Typical Characteristics

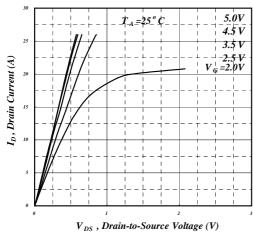


Fig 1. Typical Output Characteristics

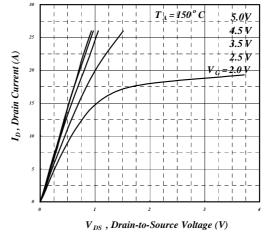


Fig 2. Typical Output Characteristics

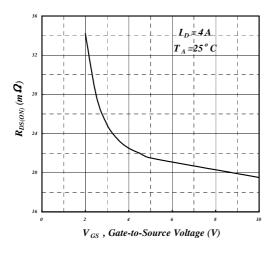


Fig 3. On-Resistance v.s. Gate Voltage

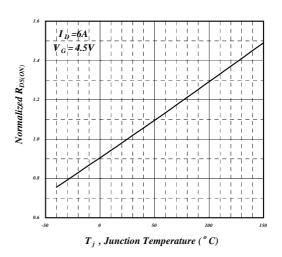


Fig 4. Normalized On-Resistance v.s. Temperature

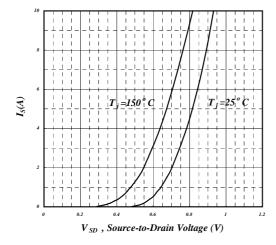


Fig 5. Forward Characteristic of Reverse Diode

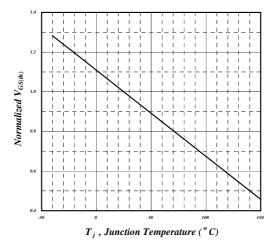


Fig 6. Gate Threshold Voltage v.s.
Junction Temperature



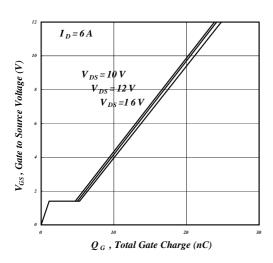


Fig 7. Gate Charge Characteristics

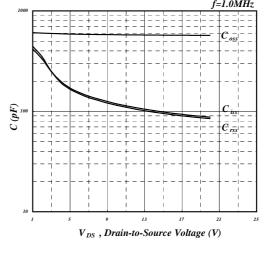


Fig 8. Typical Capacitance Characteristics

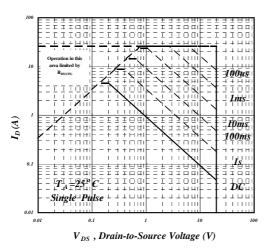


Fig 9. Maximum Safe Operating Area

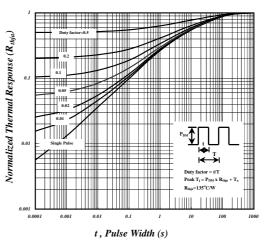


Fig 10. Effective Transient Thermal Impedance

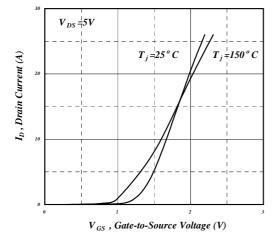


Fig 11. Transfer Characteristics

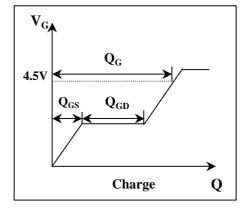
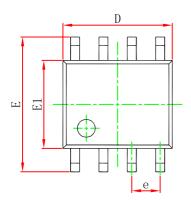
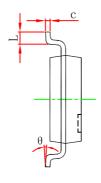


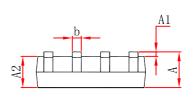
Fig 12. Gate Charge Waveform



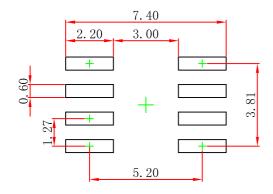
SOP-8 Package Outline Dimensions



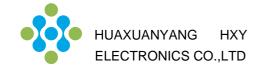




Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
A	1.350	1.750	0.053	0.069	
A1	0.100	0. 250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
c	0.170	0.250	0.007	0.010	
D	4.800	5.000	0.189	0. 197	
e	1. 270 (BSC)	0.050 (BSC)		
E	5.800	6.200	0. 228	0. 244	
E1	3.800	4.000	0.150	0. 157	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	



- Note: 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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